NUP4302MR6

Schottky Diode Array for Four Data Line ESD Protection

The NUP4302MR6 is designed to protect high speed data line interface from ESD, EFT and lighting.

Features

- Very Low Forward Voltage Drop
- Fast Switching
- PN Junction Guard Ring for Transient and ESD Protection
- ESD Rating of Class 3B (Exceeding 16 kV) per Human Body Model and Class C (Exceeding 400 V) per Machine Model
- IEC 61000−4−2 Level 4 ESD Protection
- Flammability Rating: UL 94 V−0
- Pb−Free Package is Available

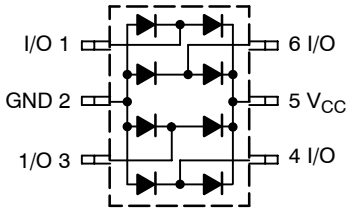
Applications

- Ultra High−Speed Switching
- USB 1.1 and 2.0 Power and Data Line Protection
- Digital Video Interface (DVI)
- Monitors and Flat Panel Displays

ON Semiconductor®

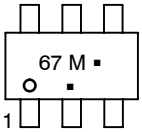
http://onsemi.com

PIN CONFIGURATION AND SCHEMATIC



TSOP−6
CASE 318G
STYLE 12

MARKING DIAGRAM



67 = Specific Device Code
M = Date Code
▪ = Pb−Free Package

(Note: Microdot may be in either location)

*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
NUP4302MR6T1	TSOP−6	3000/Tape & Reel
NUP4302MR6T1G	TSOP−6 (Pb−Free)	3000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

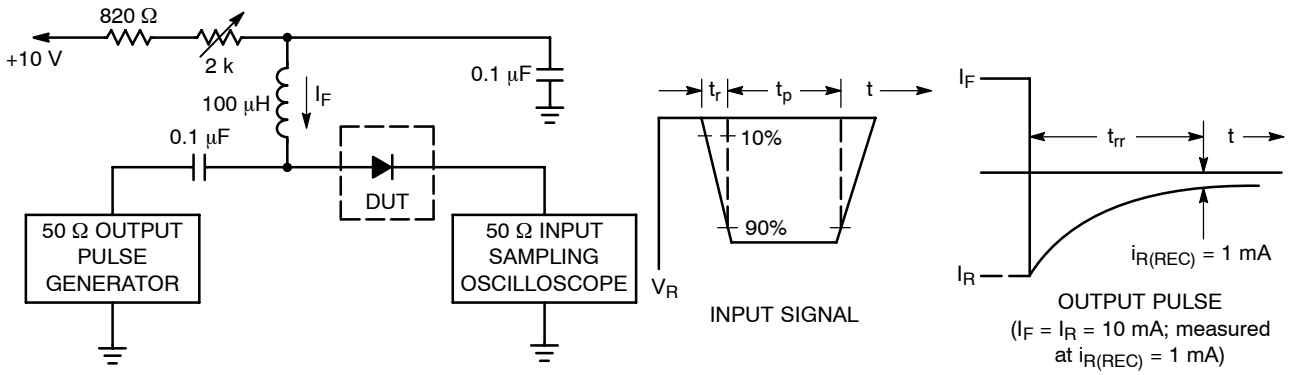
MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Peak Reverse Breakdown Voltage	V_{BR}	30	V
Forward Power Dissipation (T_A = 25°C)	P_F	225	mW
Forward Continuous Current	I_F	200	mA
Junction Operating Temperature	T_J	−55 to +125	°C
Storage Temperature Range	T_{stg}	−55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse Breakdown Voltage	V_{BR}	I_R = 100 μA	30			V
Reverse Leakage	I_R	V_R = 25 V			30	μA
Forward Voltage	V_F	I_F = 0.1 mAdc			0.28	V
Forward Voltage	V_F	I_F = 1.0 mAdc			0.35	V
Forward Voltage	V_F	I_F = 10 mAdc			0.45	V
Forward Voltage	V_F	I_F = 100 mAdc			1.00	V
Total Capacitance	C_T	V_R = 0 V, f = 1.0 MHz, I/O to Ground V_R = 0 V, f = 1.0 MHz, I/O to I/O			28 18	pF
Reverse Recovery Time	t_{rr}	I_F = I_R = 10 mA, $I_{R(REC)}$ = 1.0 mA (Figure 1)			5.0	ns



Notes: 1. A 2.0 kΩ variable resistor adjusted for a Forward Current (I_F) of 10 mA.
2. Input pulse is adjusted so $I_{R(peak)}$ is equal to 10 mA.
3. $t_p \gg t_{rr}$

Figure 1. Recovery Time Equivalent Test Circuit

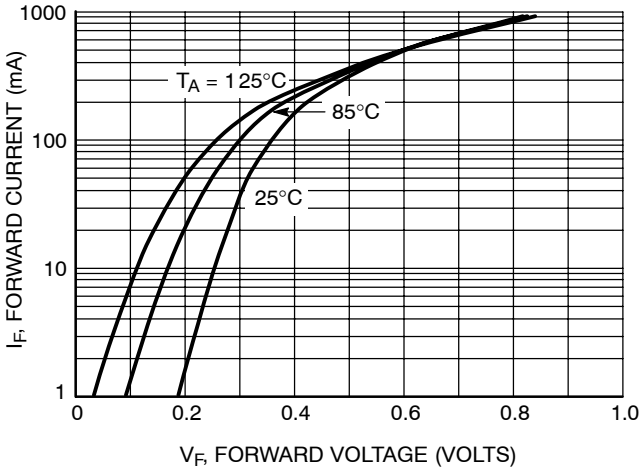


Figure 2. Forward Current as a Function of Forward Voltage; Typical Values

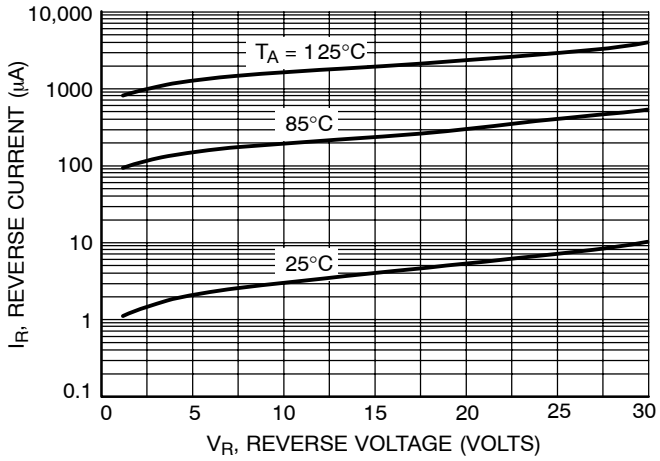


Figure 3. Reverse Current as a Function of Reverse Voltage; Typical Values

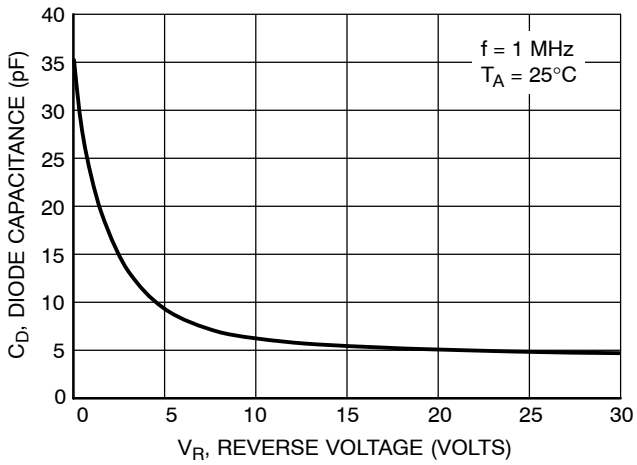
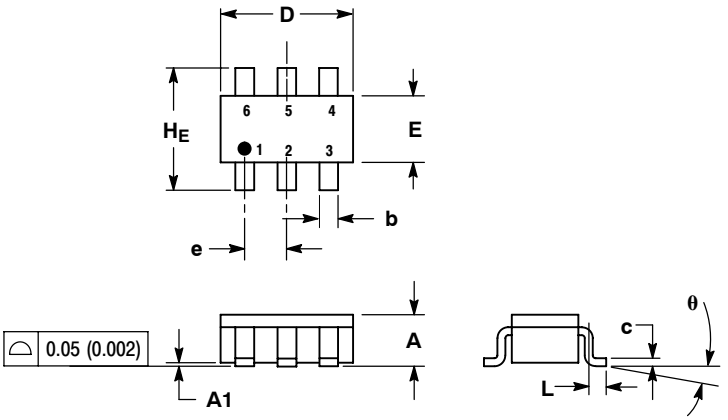


Figure 4. Diode Capacitance as a Function of Reverse Voltage; Typical Values

PACKAGE DIMENSIONS

TSOP−6
CASE 318G−02
ISSUE P

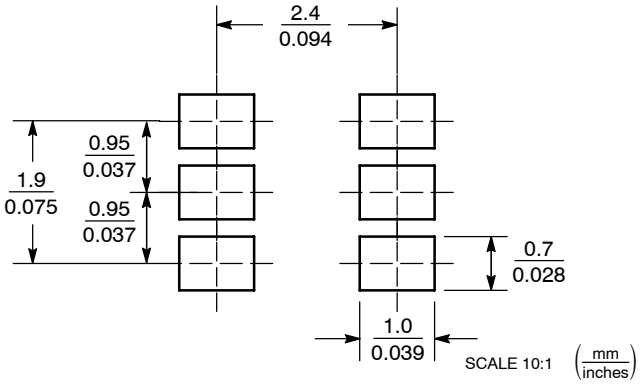


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	0.90	1.00	1.10	0.035	0.039	0.043
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.25	0.38	0.50	0.010	0.014	0.020
c	0.10	0.18	0.26	0.004	0.007	0.010
D	2.90	3.00	3.10	0.114	0.118	0.122
E	1.30	1.50	1.70	0.051	0.059	0.067
e	0.85	0.95	1.05	0.034	0.037	0.041
L	0.20	0.40	0.60	0.008	0.016	0.024
H_E	2.50	2.75	3.00	0.099	0.108	0.118
θ	0°	–	10°	0°	–	10°

STYLE 12:
PIN 1. I/O
2. GROUND
3. I/O
4. I/O
5. VCC
6. I/O

SOLDERING FOOTPRINT*



*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 61312, Phoenix, Arizona 85082−1312 USA
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Fax: 480−829−7709 or 800−344−3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800−282−9855 Toll Free USA/Canada

Japan: ON Semiconductor, Japan Customer Focus Center
2−9−1 Kamimeguro, Meguro−ku, Tokyo, Japan 153−0051
Phone: 81−3−5773−3850

ON Semiconductor Website: http://onsemi.com

Order Literature: http://www.onsemi.com/litorder

For additional information, please contact your local Sales Representative.